

**IN THE CLAIMS:**

Please amend the claims as follows:

1. (Currently Amended) A method for depositing a low dielectric constant film, comprising delivering a gas mixture comprising one or more linear, oxygen-free organosilicon compounds, one or more oxygen-free hydrocarbon compounds comprising one ring and one or two carbon-carbon double bonds in the ring, and one or more oxidizing gases comprising oxygen (O<sub>2</sub>) to a substrate surface at deposition conditions sufficient to deposit a low dielectric constant film comprising Si, O, and C on the substrate surface.
2. (Original) The method of claim 1, wherein the one or more linear, oxygen-free organosilicon compounds comprises an alkylsilane.
3. (Original) The method of claim 1, wherein the one or more linear, oxygen-free organosilicon compounds comprises a member selected from the group consisting of methylsilane, dimethylsilane, trimethylsilane, tetramethylsilane, ethylsilane, disilanomethane, bis(methylsilano)methane, 1,2-disilanoethane, 1,2-bis(methylsilano)ethane, 2,2-disilanopropane, diethylsilane, propylsilane, vinylmethylsilane, 1,1,2,2-tetramethyldisilane, hexamethyldisilane, 1,1,2,3,3-pentamethyltrisilane, 1,3-bis(methylsilano)propane, 1,2-bis(dimethylsilano)ethane, 1,3-bis(dimethylsilano)propane, and combinations thereof.
4. (Original) The method of claim 1, wherein the ring comprises five or six carbon atoms.
5. (Original) The method of claim 4, wherein the ring comprises six carbon atoms.

6. (Currently Amended) The method of claim 1, wherein the one or more oxidizing gases is further comprises a member selected from the group consisting of ozone, ~~oxygen~~, carbon dioxide, carbon monoxide, water, nitrous oxide, 2,3-butanedione, and combinations thereof.

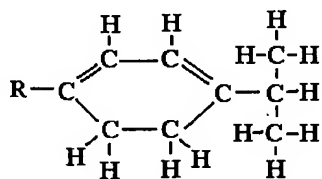
7. (Currently Amended) The method of claim ~~[[7]]~~ 6, wherein the one or more oxidizing gases consists of carbon dioxide and oxygen (O<sub>2</sub>).

8. (Currently Amended) The method of claim 1, further comprising post-treating the ~~low dielectric constant~~ film.

9. (Original) The method of claim 1, wherein the one or more linear, oxygen-free organosilicon compounds comprises trimethylsilane and the one or more oxygen-free hydrocarbon compounds comprises alpha-terpinene.

10. (Currently Amended) The method of claim 9, wherein the one or more oxidizing gases consists of carbon dioxide and oxygen (O<sub>2</sub>).

11. (Currently Amended) A method for depositing a ~~low dielectric constant~~ film, comprising delivering a gas mixture comprising one or more linear, oxygen-free organosilicon compounds, one or more oxygen-free hydrocarbon compounds including the structure:



wherein R is selected from the group consisting of linear alkane groups having one to five carbons, and one or more oxidizing gases comprising oxygen (O<sub>2</sub>) to a substrate surface at deposition conditions sufficient to deposit a ~~low dielectric constant~~ film comprising Si, O, and C on the substrate surface.

12. (Original) The method of claim 11, wherein the one or more oxygen-free hydrocarbon compounds comprises alpha-terpinene.

13. (Original) The method of claim 11, wherein the one or more linear, oxygen-free organosilicon compounds comprises a member selected from the group consisting of methylsilane, dimethylsilane, trimethylsilane, tetramethylsilane, ethylsilane, disilanomethane, bis(methylsilano)methane, 1,2-disilanoethane, 1,2-bis(methylsilano)ethane, 2,2-disilanopropane, diethylsilane, propylsilane, vinylmethylsilane, 1,1,2,2-tetramethyldisilane, hexamethyldisilane, 1,1,2,3,3-pentamethyltrisilane, 1,3-bis(methylsilano)propane, 1,2-bis(dimethylsilano)ethane, 1,3-bis(dimethylsilano)propane, and combinations thereof

14. (Original) The method of claim 11, wherein the linear alkane groups having one to five carbons are selected from the group consisting of methyl, ethyl, propyl, and isopropyl groups.

15. (Currently Amended) The method of claim 11, wherein the one or more oxidizing gases is further comprises a member selected from the group consisting of ozone, ~~oxygen~~, carbon dioxide, carbon monoxide, water, nitrous oxide, 2,3-butanedione, and combinations thereof.

16. (Currently Amended) The method of claim 11, further comprising treating the ~~low dielectric constant~~ film with an electron beam.

17. (Currently Amended) A method for depositing a ~~low dielectric constant~~ film, comprising:

delivering a gas mixture comprising:

one or more linear, oxygen-free organosilicon compounds;

one or more oxygen-free hydrocarbon compounds comprising one ring and one or two carbon-carbon double bonds in the ring;

and one or more oxidizing gases comprising oxygen (O<sub>2</sub>) to a substrate surface at deposition conditions sufficient to deposit a ~~low dielectric constant~~ film comprising Si, O, and C on the substrate surface; and  
treating the ~~low dielectric constant~~ film with an electron beam.

18. (Original) The method of claim 17, wherein the one or more linear, oxygen-free organosilicon compounds comprises a member selected from the group consisting of methylsilane, dimethylsilane, trimethylsilane, tetramethylsilane, ethylsilane, disilanomethane, bis(methylsilano)methane, 1,2-disilanoethane, 1,2-bis(methylsilano)ethane, 2,2-disilanopropane, diethylsilane, propylsilane, vinylmethylsilane, 1,1,2,2-tetramethyldisilane, hexamethyldisilane, 1,1,2,3,3-pentamethyltrisilane, 1,3-bis(methylsilano)propane, 1,2-bis(dimethylsilano)ethane, 1,3-bis(dimethylsilano)propane, and combinations thereof.

19. (Original) The method of claim 17, wherein the one or more oxygen-free hydrocarbon compounds comprises alpha-terpinene.

20. (Currently Amended) The method of claim 19, wherein the one or more linear, oxygen-free organosilicon compounds comprises trimethylsilane and the one or more oxidizing gases comprises carbon dioxide and oxygen (O<sub>2</sub>).